

## ● DEVICE MARKING

BAV99 = A7

## ● MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	70	Vdc
Forward Current	$I_F$	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Average Rectified Forward Current (1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repertitive Peak Forward Current	$I_{FSM}$		A
$t = 1.0 \mu s$		2.0	
$t = 1.0 ms$		1.0	
$t = 1.0 S$		0.5	

## ● THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	225 1.8	mW mW/ $^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	300 2.4	mW mW/ $^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ C/W$
Junction and Storage Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ C$

## ● ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ C$ unless otherwise noted) (EACH DIODE)

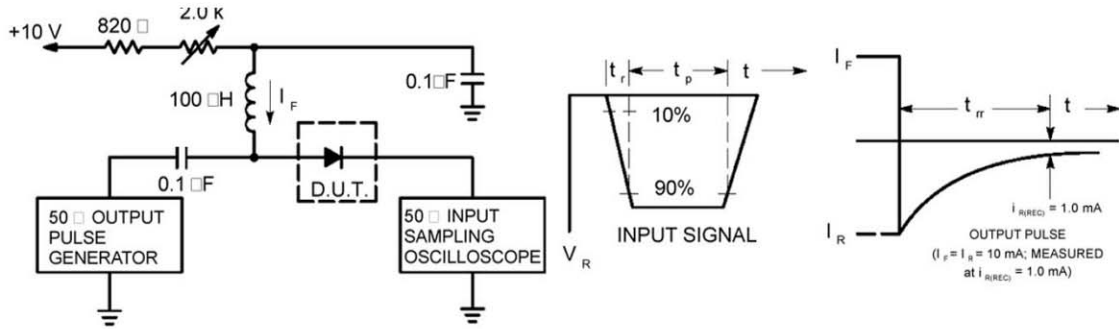
Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Reverse Breakdown Voltage ( $I_{(BR)} = 100 \mu A$ )	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ( $V_R = 70$ Vdc)	$I_R$	—	2.5	$\mu A$ dc
( $V_R = 25$ Vdc, $T_J = 150^\circ C$ )		—	30	
( $V_R = 70$ Vdc, $T_J = 150^\circ C$ )		—	50	
Diode Capacitance ( $V_R = 0$ , $f = 1.0$ MHz)	$C_D$	—	1.5	pF
Forward Voltage ( $I_F = 1.0$ mAdc)	$V_F$	—	715	mVdc
( $I_F = 10$ mAdc)		—	855	
( $I_F = 50$ mAdc)		—	1000	
( $I_F = 150$ mAdc)		—	1250	
Reverse Recovery Time ( $I_F = I_R = 10$ mAdc, $i_{R(REC)} = 1.0$ mAdc, $R_L = 100 \Omega$ ) (Figure 1)	$t_{rr}$	—	6.0	ns
Forward Recovery Voltage ( $I_F = 10$ mA, $t_r = 20$ ns)	$V_{FR}$	—	1.75	V

1. FR-5 = 1.0 x 0.75 x 0.062 in.

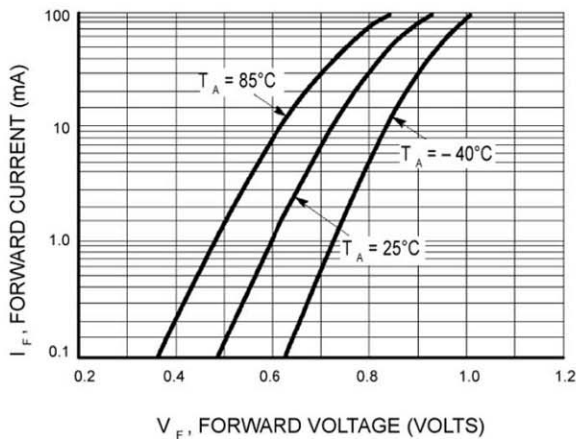
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



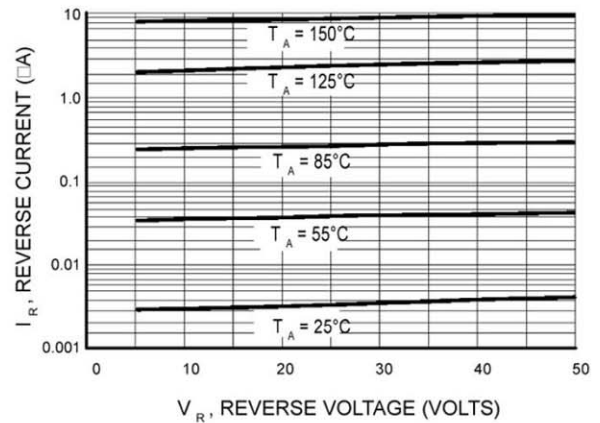
- Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

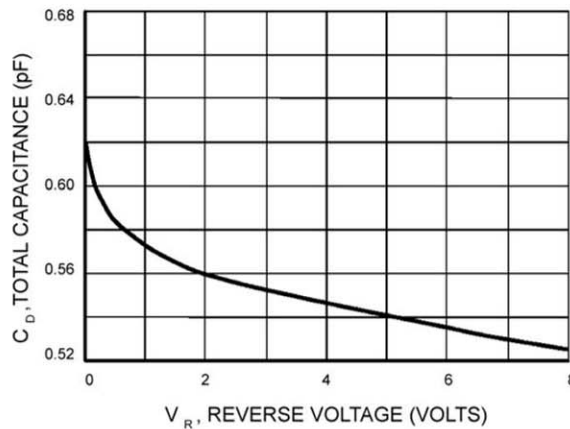
### CURVES APPLICABLE TO EACH DIODE



**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**



**Figure 4. Capacitance**